

Dual N-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
100	0.017 at $V_{GS} = 10$ V	30	16 nC

FEATURES

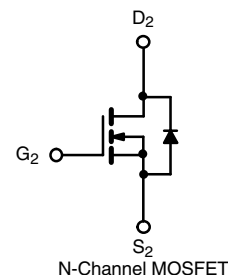
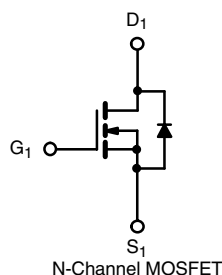
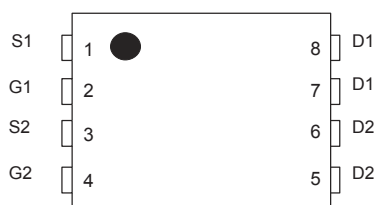
- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested


RoHS
 COMPLIANT

APPLICATIONS

- Synchronous Buck Shoot-Through Resistant
- Optimized for Primary Side Switch

Top View



ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	100	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_J = 150$ °C) ^a	I_D	$T_A = 25$ °C	30
		$T_A = 70$ °C	19
Pulsed Drain Current	I_{DM}	120	A
Continuous Source Current (Diode Conduction) ^a	I_S	30	A
Single Avalanche Current	I_{AS}	27	A
Single Avalanche Energy	E_{AS}	68	mJ
Maximum Power Dissipation ^a	P_D	$T_A = 25$ °C	49
		$T_A = 70$ °C	33
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 175	°C
Soldering Recommendations (Peak Temperature)		260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ s	56	°C/W
		Steady State	80	
Maximum Junction-to-Case (Drain)	R_{thJC}	2.1	3.0	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	1		3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 80\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 10\text{ V}$	30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$		0.017	0.022	Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 10\text{ A}$		0.020	0.028	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}$, $I_D = 10\text{ A}$		18		S
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9\text{ A}$, $V_{GS} = 0\text{ V}$		0.8	1.2	V
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = 50\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		1345		pF
Output Capacitance	C_{oss}			306		
Reverse Transfer Capacitance	C_{rss}			13		
Total Gate Charge	Q_g	$V_{DS} = 50\text{ V}$, $V_{GS} = 10\text{ V}$, $I_D = 15\text{ A}$		16	24	nC
Gate-Source Charge	Q_{gs}			3.8		
Gate-Drain Charge	Q_{gd}			5.5		
Gate Resistance	R_g			2.2		Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 50\text{ V}$, $R_L = 50\text{ }\Omega$ $I_D \cong 1\text{ A}$, $V_{GEN} = 10\text{ V}$, $R_g = 6\text{ }\Omega$		5		ns
Rise Time	t_r			3		
Turn-Off Delay Time	$t_{d(off)}$			20		
Fall Time	t_f			5		
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = 2.9\text{ A}$, $dI/dt = 100\text{ A}/\mu\text{s}$		50		

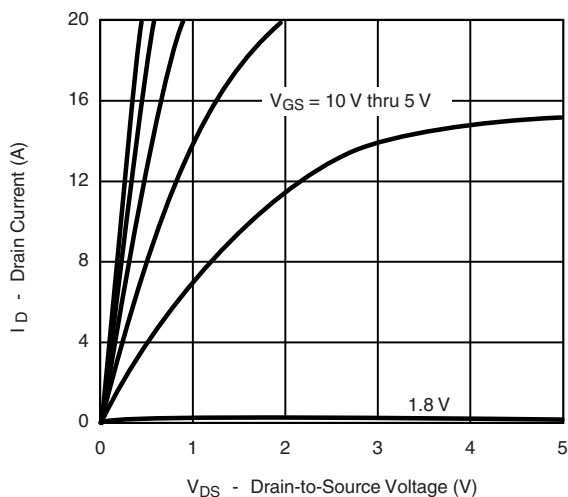
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

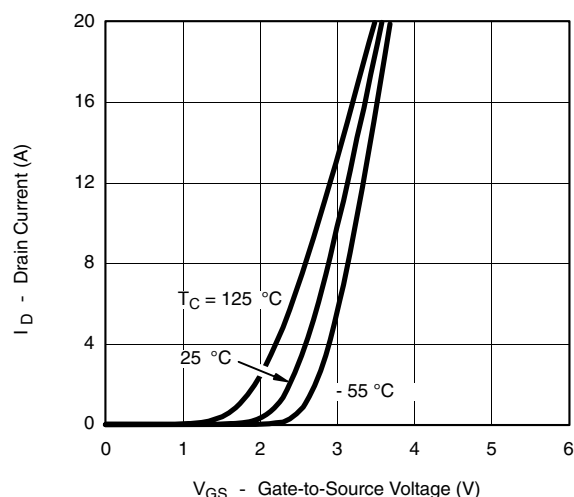
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

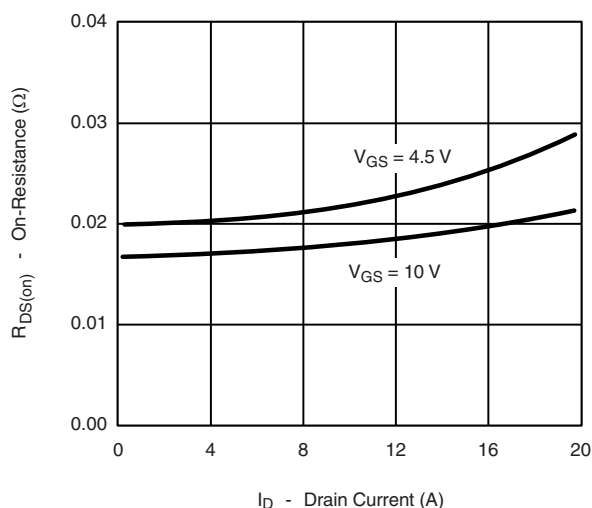
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



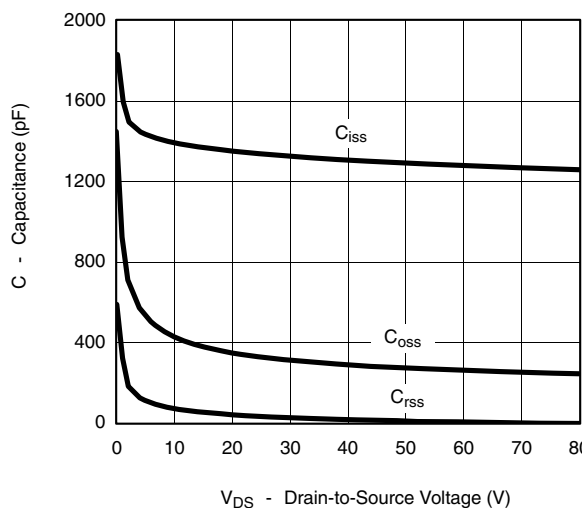
Output Characteristics



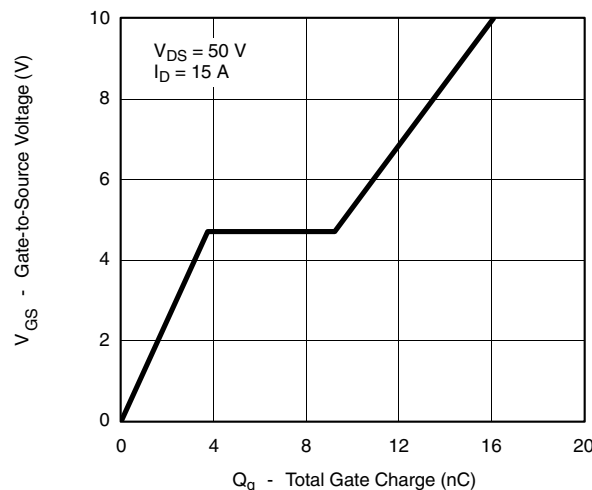
Transfer Characteristics



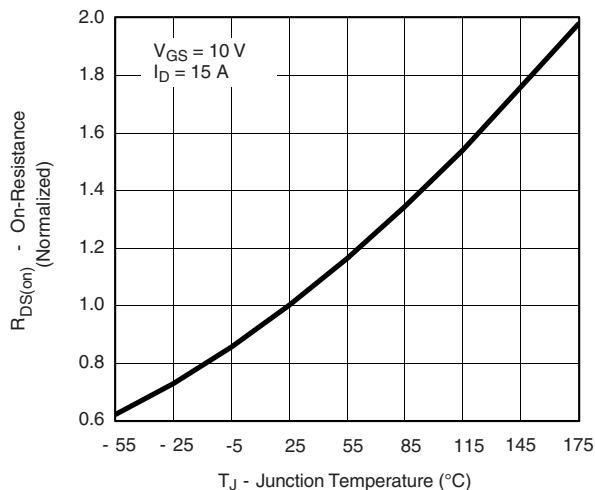
On-Resistance vs. Drain Current



Capacitance

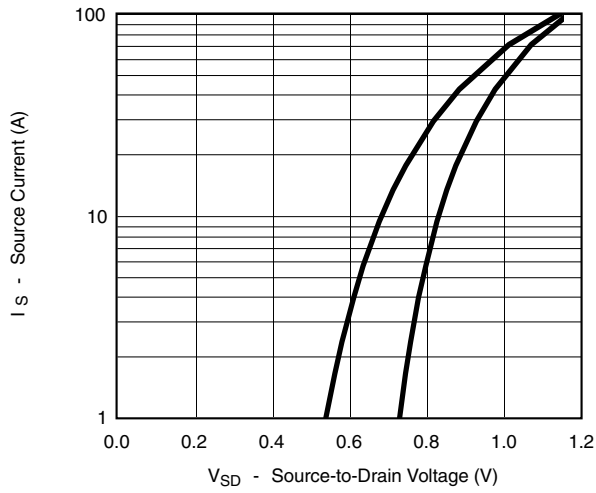


Gate Charge

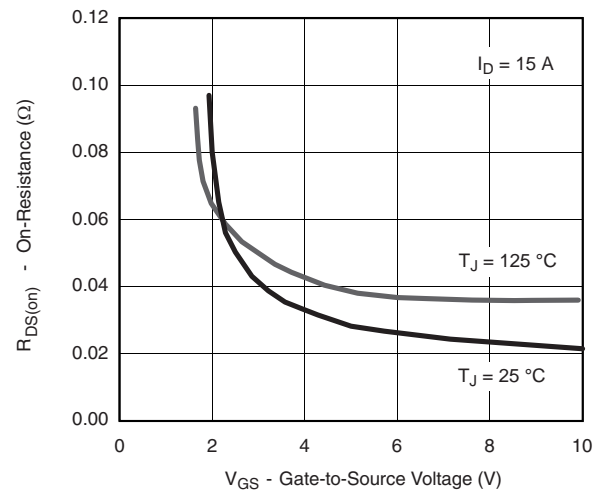


On-Resistance vs. Junction Temperature

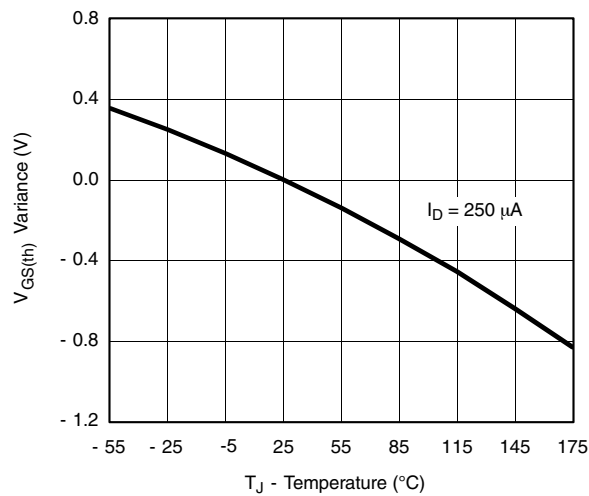
TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted



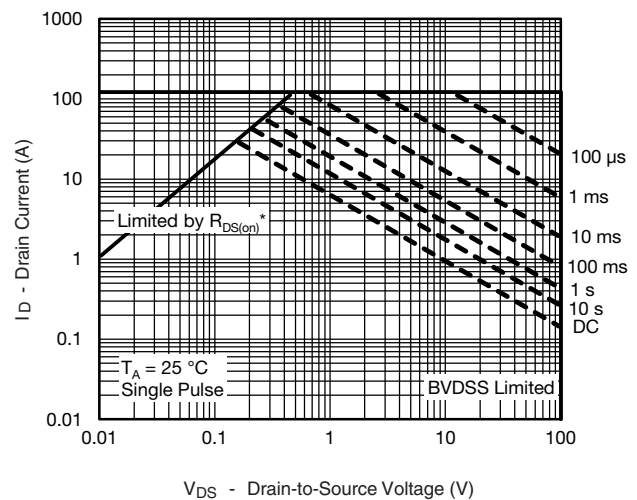
Source-Drain Diode Forward Voltage



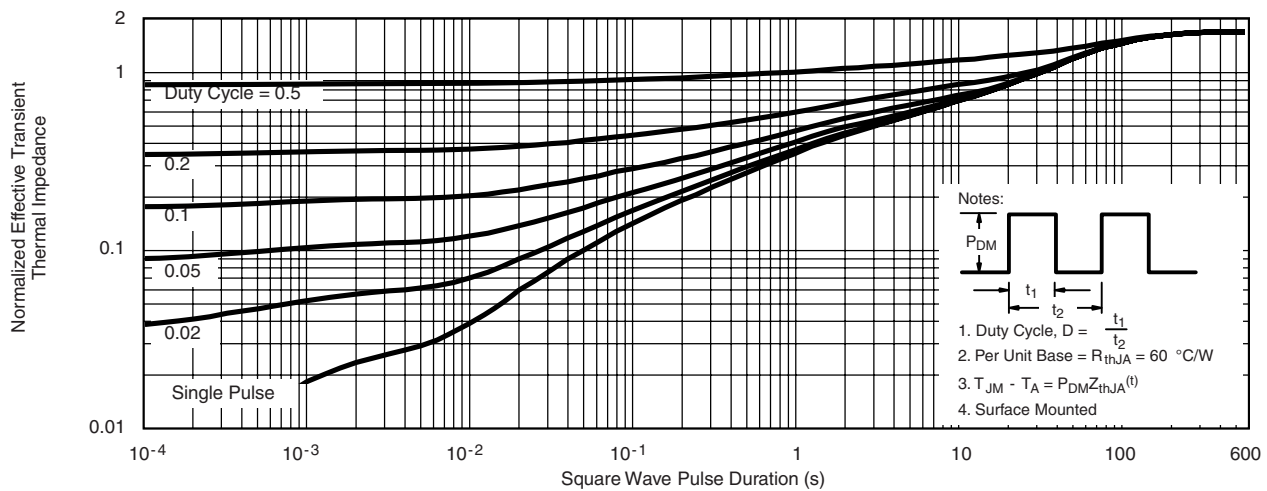
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Safe Operating Area, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient

Notes:
1. Duty Cycle, $D = \frac{t_1}{t_2}$
2. Per Unit Base = $R_{thJA} = 60\text{ }^{\circ}\text{C/W}$
3. $T_{JM} - T_A = P_{DM}Z_{thJA}^{(t)}$
4. Surface Mounted

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